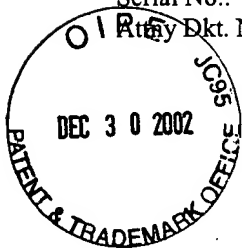


Inventor: Kennedy et al.  
Serial No.: 09/547,167  
Att. Dkt. No. 100595.0052US1

Art Unit: 2822  
Examiner: C. Novacek



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
WASHINGTON, D.C. 20231

#12  
#12/12/03  
Q7rel  
1/13/03

Inventor: **Kennedy et al.**  
Serial No: **09/547,167**  
Filed: **April 11, 2000**  
For: **The Use of Sacrificial  
Inorganic Dielectrics for  
Dual Damascene Processes  
Utilizing Organic Intermetal  
Dielectrics**

Examiner: C. Novacek  
Art Unit: 2822

Attorney Docket No.: 100595.0052US1

**RECEIVED**

JAN 02 2003

**OFFICE OF PETITIONS**

**PRELIMINARY AMENDMENT**

**IN THE CLAIMS**

Please find below a Clean Copy of Claims for Examiner's Immediate Reference. A Marked Up Copy and Additional Clean Copy are herein attached.

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1. (Twice Amended) A method of making conducting vias and conducting lines on a substrate comprising:
- depositing a stack having a top surface on a substrate, wherein the stack comprises a first organic intermetal dielectric layer and a hardmask layer, wherein the hardmask layer comprises a material comprising silicon oxynitride or silicon oxide;
- forming a via opening in said stack;
- depositing a sacrificial inorganic dielectric in the via opening, wherein the sacrificial inorganic dielectric substantially filling the via opening and substantially covering the top surface of the stack;